

## P-Channel 100 V (D-S) MOSFET

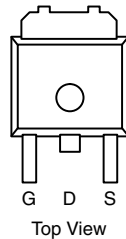
PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)
- 100	0.043 at V <sub>GS</sub> = - 10 V	- 37	54 nC
	0.048 at V <sub>GS</sub> = - 4.5 V	- 35	

### FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

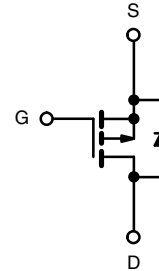


**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

**TO-252**


Drain Connected to Tab

**Ordering Information:**  
SUD50P10-43L-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	- 100	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>b</sup>	I <sub>D</sub>	T <sub>C</sub> = 25 °C	- 36.4	
		T <sub>C</sub> = 70 °C	- 29.1	
		T <sub>A</sub> = 25 °C	- 9 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	- 7.2 <sup>b, c</sup>	
Pulsed Drain Current	I <sub>DM</sub>	- 40	A	
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	T <sub>C</sub> = 25 °C		- 50 <sup>a</sup>
		T <sub>A</sub> = 25 °C		- 5.75 <sup>b, c</sup>
Avalanche Current	I <sub>AS</sub>	- 35		mJ
Single Pulse Avalanche Energy	E <sub>AS</sub>	61		
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	113.6	
		T <sub>C</sub> = 70 °C	72.7	
		T <sub>A</sub> = 25 °C	6.9 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	4.4 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	t ≤ 10 s	15	18
		Steady State	40	50
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.85	1.1	°C/W

Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 50 °C/W.

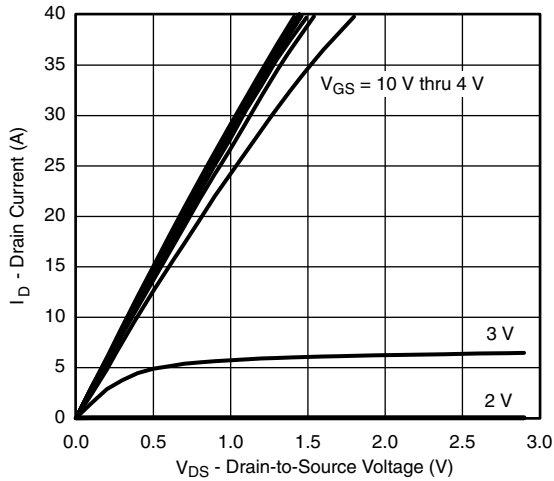
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)								
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit		
<b>Static</b>								
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-100			V		
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-109		mV/ $^\circ\text{C}$		
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			5.9				
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1		-3	V		
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA		
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$		
		$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10			
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = -10\text{ V}$	-40			A		
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -9.2\text{ A}$		0.036	0.043	$\Omega$		
		$V_{GS} = -4.5\text{ V}, I_D = -7.7\text{ A}$		0.040	0.048			
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -15\text{ V}, I_D = -9.2\text{ A}$		38		S		
<b>Dynamic<sup>b</sup></b>								
Input Capacitance	$C_{iss}$	$V_{DS} = -50\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		4600		pF		
Output Capacitance	$C_{oss}$			230				
Reverse Transfer Capacitance	$C_{rss}$			175				
Total Gate Charge	$Q_g$	$V_{DS} = -50\text{ V}, V_{GS} = -10\text{ V}, I_D = -9.2\text{ A}$		106	160	nC		
				54	81			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -50\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -9.2\text{ A}$		14				
Gate-Drain Charge	$Q_{gd}$			26				
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		4		$\Omega$		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50\text{ V}, R_L = 6.5\text{ }\Omega$ $I_D \cong -7.7\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		15	25	ns		
Rise Time	$t_r$			20	30			
Turn-Off Delay Time	$t_{d(off)}$			110	165			
Fall Time	$t_f$			100	150			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50\text{ V}, R_L = 6.5\text{ }\Omega$ $I_D \cong -7.7\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		42	65	ns		
			Rise Time	$t_r$			160	240
			Turn-Off Delay Time	$t_{d(off)}$			100	150
			Fall Time	$t_f$			100	150
<b>Drain-Source Body Diode Characteristics</b>								
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			-50	A		
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				-40			
Body Diode Voltage	$V_{SD}$	$I_S = -7.7\text{ A}$		-0.8	-1.2	V		
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -7.7\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		60	90	ns		
Body Diode Reverse Recovery Charge	$Q_{rr}$			150	225	nC		
Reverse Recovery Fall Time	$t_a$			46		ns		
Reverse Recovery Rise Time	$t_b$			14				

## Notes:

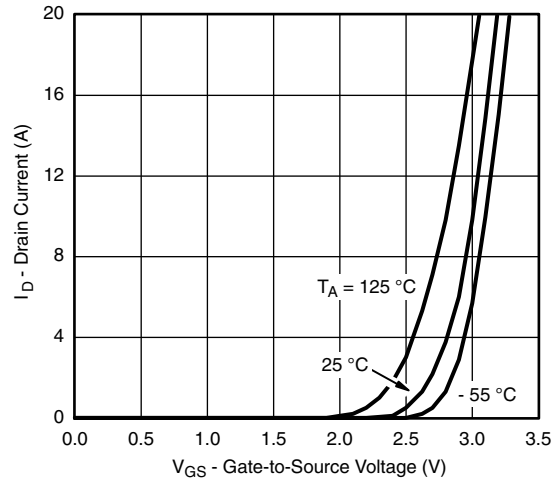
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

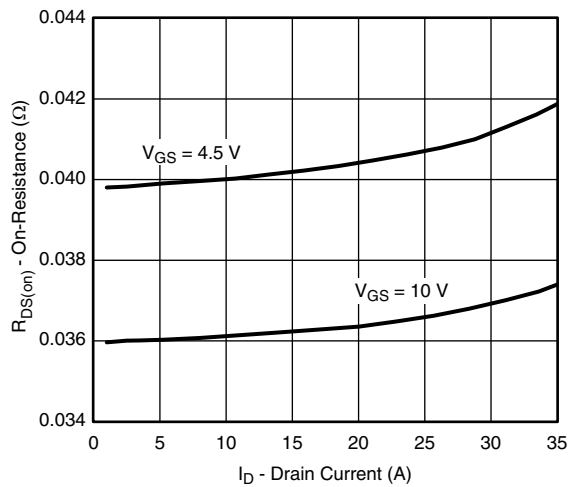
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



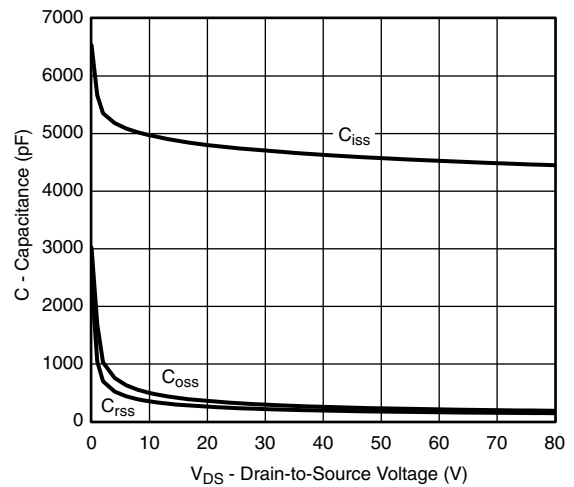
**Output Characteristics**



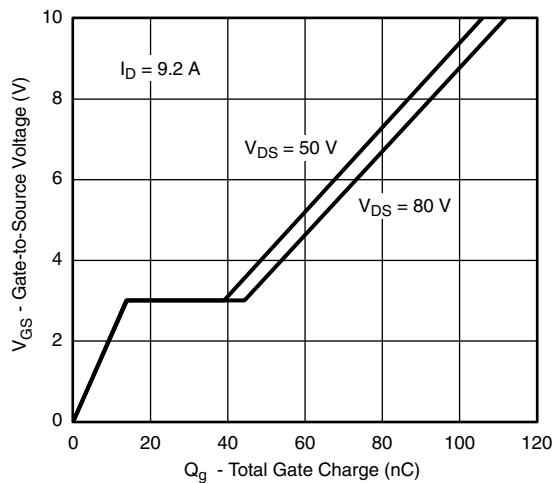
**Transfer Characteristics**



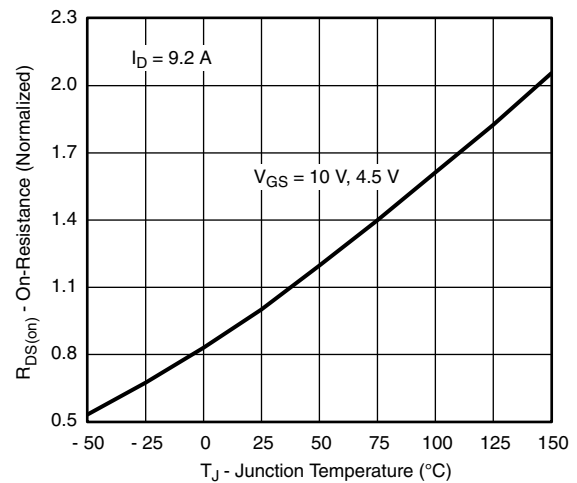
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**

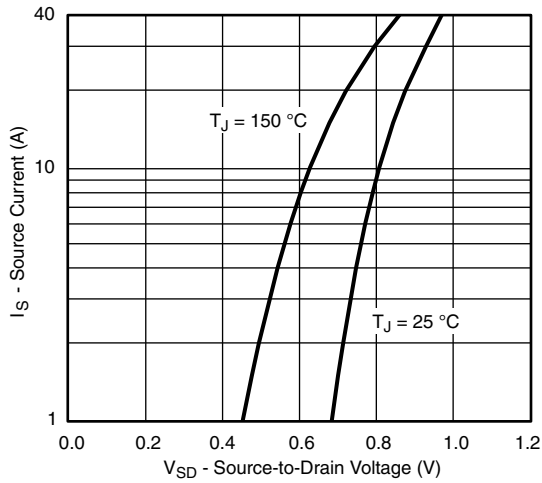


**Gate Charge**

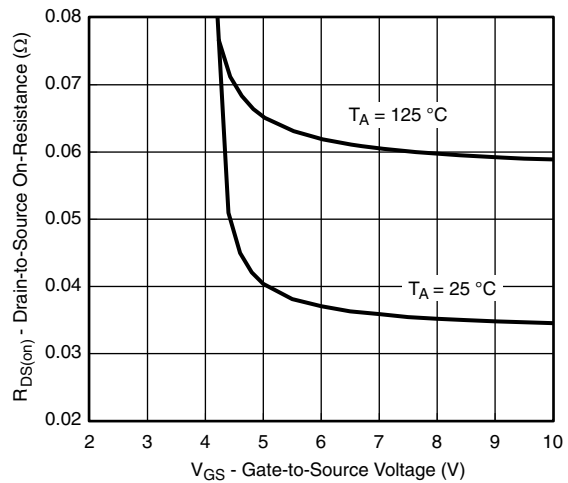


**On-Resistance vs. Junction Temperature**

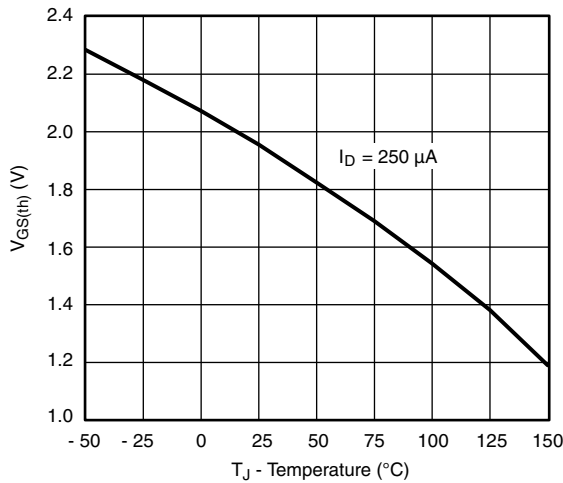
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



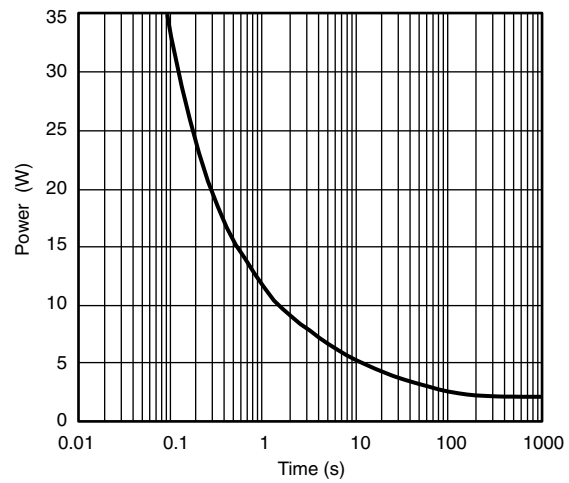
Source-Drain Diode Forward Voltage



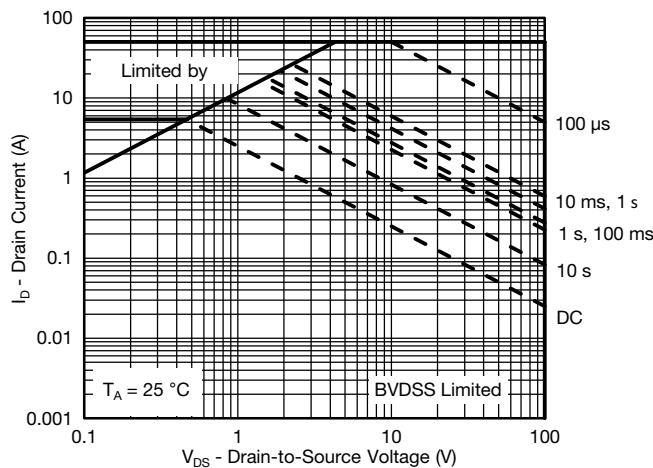
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



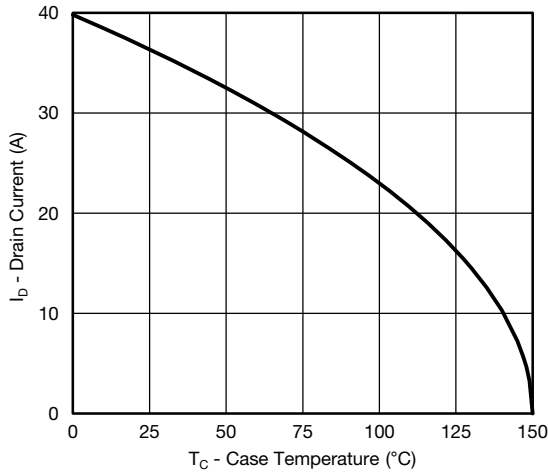
Single Pulse Power, Junction-to-Ambient



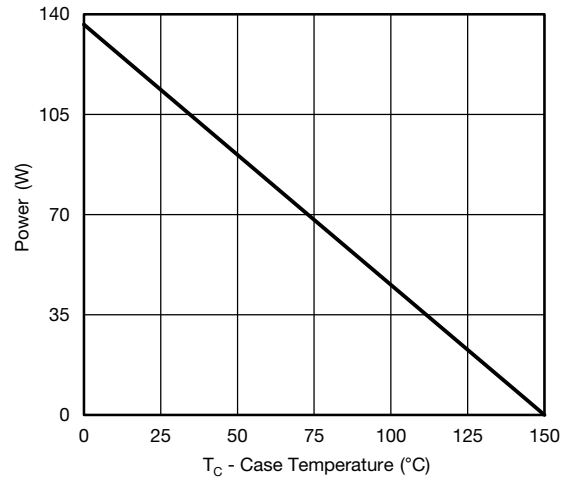
\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area, Junction-to-Ambient

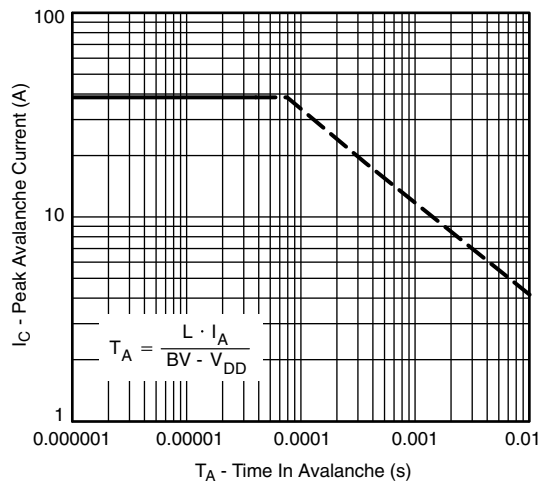
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating\***



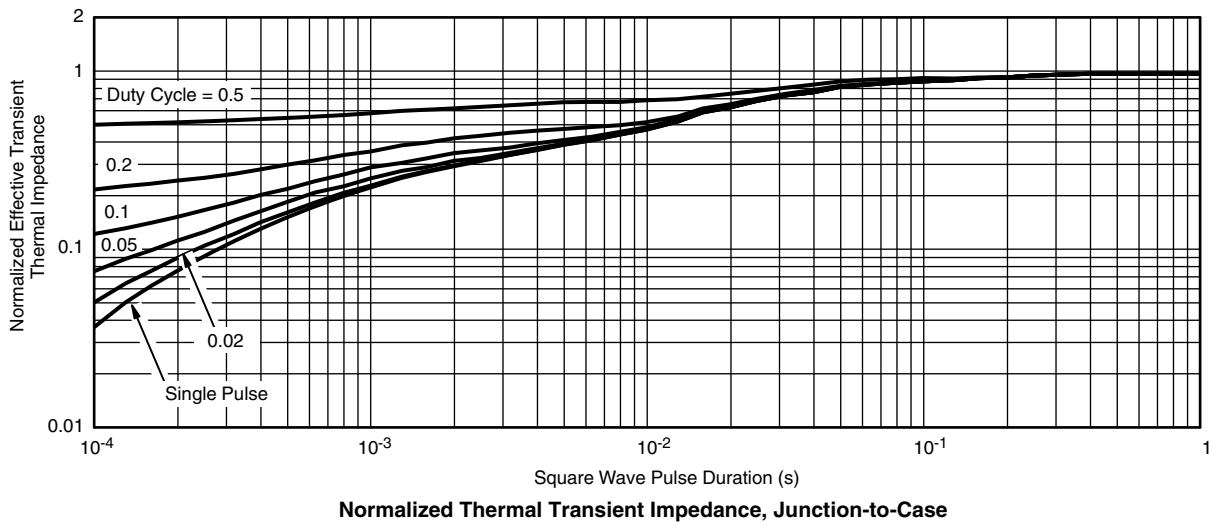
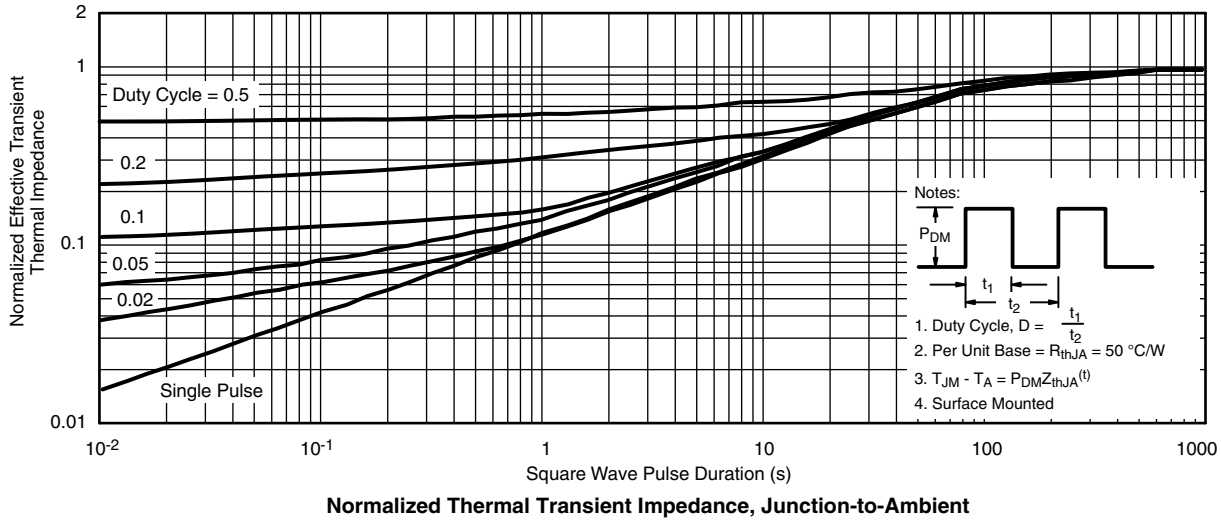
**Single Pulse Power, Junction-to-Ambient**



**Single Pulse Avalanche Capability**

\* The power dissipation P<sub>D</sub> is based on T<sub>J(max.)</sub> = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



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# TO-252AA Case Outline

## VERSION 1: FACILITY CODE = Y



MILLIMETERS		
DIM.	MIN.	MAX.
A	2.18	2.38
A1	-	0.127
b	0.64	0.88
b2	0.76	1.14
b3	4.95	5.46
C	0.46	0.61
C2	0.46	0.89
D	5.97	6.22
D1	4.10	-
E	6.35	6.73
E1	4.32	-
H	9.40	10.41
e	2.28 BSC	
e1	4.56 BSC	
L	1.40	1.78
L3	0.89	1.27
L4	-	1.02
L5	1.01	1.52

### Note

- Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



DIM.	MILLIMETERS	
	MIN.	MAX.
A	2.18	2.39
A1	-	0.13
b	0.65	0.89
b1	0.64	0.79
b2	0.76	1.13
b3	4.95	5.46
c	0.46	0.61
c1	0.41	0.56
c2	0.46	0.60
D	5.97	6.22
D1	5.21	-
E	6.35	6.73
E1	4.32	-
e	2.29 BSC	
H	9.94	10.34

DIM.	MILLIMETERS	
	MIN.	MAX.
L	1.50	1.78
L1	2.74 ref.	
L2	0.51 BSC	
L3	0.89	1.27
L4	-	1.02
L5	1.14	1.49
L6	0.65	0.85
θ	0°	10°
θ1	0°	15°
θ2	25°	35°

Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022  
 DWG: 5347



## RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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